Parity effect in superconducting aluminum single electron transistors with spatial gap profile controlled by film thickness

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(Dated: February 2, 2006)

We propose a novel method for suppression of quasiparticle poisoning in Al Coulomb blockade devices. The method is based on creation of a proper energy gap profile along the device. In contrast to the previously used techniques, the energy gap is controlled by the film thickness. Our transport measurements confirm that the quasiparticle poisoning is suppressed and clear 2e periodicity is observed only when the island is made much thinner than the leads. This result is consistent with the existing model and provides a simple method to suppress quasiparticle poisoning.

Parity effect in a small superconducting island, whether it contains an unpaired electron (quasiparticle, QP) or not, has been extensively studied in 1990s. Recently, this topic has attracted research interest again because of its importance for the quantum bit (qubit) application of the small Josephson junction circuits. It is well known that the superconducting charge qubit is least sensitive to the main particle, QP) or not, has been extensively studied in whether it contains an unpaired electron (quasiparticle, QP) or not, has been extensively studied in

Fig. 1: (a) Schematic diagram of the energy bands of the charge qubit as a function of \( n_g \). Dashed lines represent the energy bands for the odd parity state. (b) Spatial superconducting gap profile, which is favorable for the QP-poisoning-free SET device. (c) Scanning electron micrograph of the SET sample, whose island and leads are 10 and 50 nm thick, respectively. The gate electrode is not seen in this picture.

Recently, Aumentado et al. reported that it is possible to reproducibly obtain 2e periodicity of the supercurrent in the superconducting Al SET by making \( \Delta \) of the island higher than that of the leads (Fig. 1b), because it works as a barrier, which prevent nonequilibrium QPs in the leads from entering the island. They realized such a spatial profile of \( \Delta \) by introducing a small amount of oxygen during the evaporation of the island. Similar effect has been reported for a Cooper-pair box where the required spatial profile is obtained by a weak magnetic field applied parallel to the film. Motivated by these works, we investigate an alternative way of creating a proper \( \Delta \) profile. Our approach is based on the fact that \( \Delta \) of an Al thin film depends also on the film thickness. This suggests that we can obtain the spatial profile of \( \Delta \) by choosing a proper thickness for the island and the leads. This technique is simpler than controlling oxygen pressure or magnetic field. Moreover, improper choice of the thickness may lead to the QP-poisoned devices. Our results show that the \( \Delta \) profile controlled by the film thickness can change the degree of QP poisoning.

The SET samples were fabricated by electron-beam lithography and double-angle evaporation of Al using a trilayer resist (methylmethacrylate-methacrylic acid (MMA-MAA)/Ge/poly-methyl-methacrylate (PMMA), 200/20/50 nm thick) on an oxidized Si wafer with pre-deposited gold pads. The pressure inside the chamber before Al evaporation does not exceed 4 x 10^-8 Torr, and increases up to 1 x 10^-7 Torr during the evaporation. No oxygen doping during the Al evaporation was performed in this study. The surface of the first Al layer was oxidized by 70 mTorr oxygen for 0.7 to 5 min. Figure 1c shows a scanning electron micrograph of one of the SET devices with the thickness of 10 nm and 50 nm for the island and the leads, respectively. The bright area is
the evaporated Al. The source, drain and gate electrodes are connected to the gold pads, which are about 20 μm away. No QP traps are used in the present study.

In the following, we show two kinds of experiments. In the first experiment, we investigate the dependence of Δ on the film thickness by measuring the current-voltage (I − V) characteristic of the SET. For this experiment, smaller E_j/E_c ratio is desirable for better accuracy in Δ (see below). In the second experiment, we investigate the gate modulation of the SET supercurrent with various thicknesses. Experimentally, it becomes easier to observe supercurrent, if the E_j/E_c ratio of the SET is larger. Therefore we prepared two sets of SET devices: one with small E_j/E_c ratio (∼ 10^{-2}) and the other with large E_j/E_c ratio (∼ 10^{-1}), by changing the junction area and the oxidation time.

In the first experiment, we use small E_j/E_c ratio samples. They have typically normal source-drain resistance R_{sd} = 260 kΩ and E_c = 340 μeV. We fabricate SET devices with the thickness of the island (t_i) ranging from 10 to 50 nm. The thickness of the leads (t_l) is always 50 nm. Using a 3He refrigerator at temperatures of ∼ 300 mK, we measure the source-drain current (I_{sd}) as a function of the gate voltage (V_g) for different values of fixed source-drain bias voltage (V_{sd}), as it is exemplified in an intensity plot in Fig. 2b for the sample with t_i = 40 nm. One can see a clear Coulomb blockade diamond structure: a sharp rise of the QP tunneling current above the Coulomb blockade threshold voltage V_{th} which is modulated by V_g. From the modulation period, we estimate the capacitance between the gate electrode and the island C_g to be 8.1 aF. The arrays of peaks and dips parallel to the diamond structure are due to Josephson-quasiparticle cycles. As shown in the figure, V_{th} is modulated between 2(Δ(t_l) + Δ(t_i)) and 2(Δ(t_l) + Δ(t_i)) + 2E_c, where Δ(t) is the superconducting gaps of the Al thin film with the thickness t. Thus, we can determine the value of Δ(t_l) + Δ(50 nm) from this measurement and Δ(50 nm) can be determined from the similar measurement for the sample with t_i of 50 nm, which turned out to be 0.2 meV on average. The derived Δ(t) is plotted in Fig. 2a. It is observed that Δ increases as t is decreased, especially below 20 nm. This is qualitatively consistent with the previous reports.[19] The thinnest sample in this study gives 20 to 25% higher Δ as compared to Δ(50 nm). This variation of Δ is as high as the one achieved by oxygen doping in Ref. 6, indicating that we can create a similar spatial profile of Δ in the SET by controlling the film thickness. In the next experiment, we check the effect of the Δ profile on the periodicity of the SET supercurrent.

FIG. 2: (a) Intensity plot of I_{sd} as functions of V_g and V_{sd}. The device has 40 nm thick island and 50 nm thick leads. (b) Observed superconducting energy gap of Al as a function of the film thickness.

**TABLE I: Sample parameters of large E_j/E_c ratio samples.**

<table>
<thead>
<tr>
<th>Sample</th>
<th>R_{sd} [kΩ]</th>
<th>E_c [μeV]</th>
<th>E_j [μeV]</th>
<th>Δ/Vg (mV)</th>
<th>period (nm)</th>
</tr>
</thead>
<tbody>
<tr>
<td>10/50a</td>
<td>52</td>
<td>145</td>
<td>27</td>
<td>2c</td>
<td></td>
</tr>
<tr>
<td>10/50b</td>
<td>53</td>
<td>141</td>
<td>27</td>
<td>2c</td>
<td></td>
</tr>
<tr>
<td>10/30</td>
<td>38</td>
<td>139</td>
<td>37</td>
<td>2c</td>
<td></td>
</tr>
<tr>
<td>40/50</td>
<td>32</td>
<td>114</td>
<td>40</td>
<td>2c</td>
<td></td>
</tr>
<tr>
<td>50/10</td>
<td>47</td>
<td>160</td>
<td>30</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

Based on the result of the first experiment, we fabricate SET devices (large E_j/E_c ratio) with several combinations of t_i and t_l, by which we will denote the samples as t_i/t_l hereafter. Sample parameters are summarized in Table I. In all samples, the thinner layer was evaporated first. The measurements were performed in a dilution refrigerator at a base temperature of 50 mK using CuNi...
coaxial cables with $RC$ filters as dc lines. Using the current-biased configuration, we swept $I_d$ at a rate of $\sim 0.1$ nA/s and measured $V_{sd}$ for different values of fixed $V_g$. Here we show the results of such measurements for two samples, which have opposite $\Delta$ profiles: the sample 10/50a (higher $\Delta$ for the island) in Fig. 4a, and the sample 50/10 (higher $\Delta$ for the leads) in Fig. 4b. Each curve in the panels is offset by 0.1 nA for clarity. In Fig. 4a, current steps are observed near zero $V_{sd}$, to which we attribute the supercurrent. They are modulated by $V_g$ and the period is twice larger than that of QP tunneling current observed at higher $V_{sd}$, indicating that the supercurrent is $2\pi$ periodic. In Fig. 4b, we observe the QP tunneling current modulated by $V_g$, but the supercurrent is hardly observed.

From these measurements, we obtained the switching current $I_s$ and plotted as a function of the reduced gate charge $n_g = C_g V_g/2e$ for all the samples in Fig. 4c. Here, $I_s = \pi \Delta_{eff}/2eR_N$ is the Ambegaokar-Baratoff critical current, $R_N$ is the normal-state resistance of the single junction, and $\Delta_{eff} = 2\Delta(t_i)\Delta(t_f)/\Delta(t_i) + \Delta(t_f)$.

We assume that both junctions in the SET have the same resistance. We observe clear $2\pi$ periodicity in the samples 10/50a, 10/50b and 10/30. In all these samples, $\Delta$ of the island is about 20% higher than that of the leads. In the sample 40/50, we still see the $2\pi$ periodicity, but the contrast of the gate modulation becomes small. In the sample 50/10, one QP state is favorable in a wider range, $0.13 < n_g < 0.87$, which leads to the poisoning of the supercurrent. Although we expect the gate modulation of $I_s$ with $1\pi$ periodicity, it is not clearly observed probably because the magnitude of $I_s$ is so small that it can be easily smeared out by the external noise.

In summary, by measuring the $I-V$ characteristics of the SET, we have shown that $\Delta$ of Al depends on the film thickness. We have measured the gate modulation of the supercurrent of the SET devices, whose spatial profiles of $\Delta$ were controlled by the film thickness. Clear $2\pi$ periodicity is observed only when the island is much thinner than the leads, demonstrating that the $\Delta$ profile controlled by the film thickness can help to suppress QP poisoning.

The authors would like to thank T. Duty, D. B. Havidan, H. Im, A. O. Niskanen and M. Watanabe for fruitful discussions. This work was partially supported by the Japan Science and Technology Corporation.

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17 The data in Fig. 2b is obtained from the peak position of $dl_{SD}/dv_{SD}$.


19 Strictly speaking, we also need to take into account $E_J$. However, with the present value of $E_J/E_c$ ratio, its effect on $n_{so}$ is negligibly small ($< 0.005$).
Another reason for the observed small $2I_s/I_0$ is insufficient filtering for the external noise in the measurement lines.